

IN THE CLAIMS:

Claims 1-19 have been amended herein. All of the pending claims 1 through 19 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A selective method for cleaning material from a wafer comprising:

providing an ~~etchant~~etchant-dispensing apparatus having an inlet thereto for an etchant agent and a tubular member having at least one thin annular edge thereon; placing an area of ~~said~~ the wafer within an annular member of ~~said~~ the ~~etchant~~etchant-dispensing apparatus, ~~said~~ at least one thin annular edge of ~~said~~ the annular member of ~~said~~ the ~~etchant~~etchant-dispensing apparatus located adjacent a portion of ~~said~~ the wafer; aligning ~~said~~ the wafer and ~~said~~ the ~~etchant~~etchant-dispensing apparatus; dispensing an etchant onto ~~said~~ at least one the area of ~~said~~ the wafer ~~by using the said etchant~~ etchant-dispensing apparatus; and removing ~~said~~ the etchant.

2. (Currently Amended) The method of claim 1, wherein ~~said~~ placing includes aligning ~~said~~ the wafer in a substantially perpendicular position in relation to ~~said~~ the ~~etchant~~etchant-dispensing apparatus.

3. (Currently Amended) The method of claim 1, wherein ~~said~~ aligning comprises aligning ~~said~~ the wafer to ~~said~~ the ~~etchant~~etchant-dispensing apparatus.

4. (Currently Amended) The method of claim 1, wherein ~~said~~ aligning comprises aligning ~~said~~ the ~~etchant~~etchant-dispensing apparatus to ~~said~~ the wafer.

5. (Currently Amended) The method of claim 1, wherein ~~said aligning~~ comprises aligning ~~said the~~ wafer substantially perpendicular to ~~said the~~ at least one thin annular edge of ~~said the~~ annular member of ~~said the etchant~~ ~~etchant~~-dispensing apparatus.

6. (Currently Amended) The method of claim 1, wherein ~~said aligning~~ includes aligning ~~said the~~ at least one thin annular edge of ~~said the~~ annular member of ~~said the etchant~~ ~~etchant~~-dispensing apparatus substantially perpendicular to ~~said a portion of said the~~ wafer adjacent ~~said at least one~~ ~~the~~ area thereon.

7. (Currently Amended) The method of claim 1, wherein ~~said the~~ material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

8. (Currently Amended) The method of claim 7, wherein ~~said the~~ metal material includes a refractory metal.

9. (Currently Amended) The method of claim 1, wherein ~~said removing said the~~ etchant includes removal of ~~said the~~ etchant by one of suction and vacuum.

10. (Currently Amended) The method of claim 1, further comprising cleaning a surface of ~~said the~~ wafer.

11. (Currently Amended) The method of claim 10, wherein ~~the cleaning said the surface of the~~ wafer includes:

cleaning ~~a~~ ~~the~~ surface of ~~said the~~ wafer with a cleaning agent; and rinsing ~~said the~~ wafer in deionized water.

12. (Currently Amended) The method of claim 1, wherein ~~said the~~ etchant includes at least one of a liquid, a liquid vapor, a gas, ammonia, hydrogen fluoride, nitric acid, hydrogen peroxide, ammonium fluoride, and mixtures thereof.

13. (Currently Amended) A selective cleaning method for removing a material from a wafer for a semiconductor fabrication process, ~~said process~~ the method comprising: chemical mechanical planarizing ~~said the~~ wafer prior to ~~said~~ removing of ~~said the~~ material from ~~said the~~ wafer; providing an etchant-etchant-dispensing apparatus having a tubular member, an annular member having ~~at least~~ least one thin annular edge thereon, and an inlet for etchant; aligning at least one area of ~~said the~~ wafer and at least a portion of ~~said the~~ etchant-etchant-dispensing apparatus; dispensing ~~said an~~ etchant onto ~~said the~~ at least one area of ~~said the~~ wafer; and removing ~~said the~~ etchant using a portion of ~~said the~~ etchant-etchant-dispensing apparatus.

14. (Currently Amended) The method of claim 13, wherein ~~said~~ aligning includes one of aligning a portion of ~~said the~~ wafer in a substantially perpendicular position in relation to ~~said the~~ etchant-etchant-dispensing apparatus, aligning a portion of ~~said the~~ wafer to ~~said the~~ etchant-etchant-dispensing apparatus, aligning ~~said the~~ etchant-etchant-dispensing apparatus to ~~said the~~ wafer, and aligning ~~said the~~ wafer substantially perpendicular to ~~said the~~ at least one thin annular edge of ~~said annular member of the~~ etchant-etchant-dispensing apparatus.

15. (Currently Amended) The ~~process~~ method of claim 13, wherein ~~said the~~ material includes at least one of chemical mechanical planarization process slurry material, a metal material, a photoresist material, a dielectric material, and a polysilicon material.

16. (Currently Amended) The ~~process~~ method of claim 15, wherein ~~said the~~ metal material includes a refractory metal.

17. (Currently Amended) The process method of claim 13, wherein said removing said the etchant includes removal of said the etchant by one of suction and vacuum.

18. (Currently Amended) The process method of claim 13, further comprising cleaning a surface of said the wafer.

19. (Currently Amended) The process method of claim 18, wherein the step of cleaning said a surface of the wafer includes:
cleaning said the surface of the wafer with a cleaning agent; and
rinsing said the wafer in deionized water.